Abstracts

Modeling a New Generation of RF Devices: MOSFETs for L-Band Applications

J.C. Costa, D. Lovelace, D. Ngo and N. Camilleri. "Modeling a New Generation of RF Devices: MOSFETs for L-Band Applications." 1993 MTT-S International Microwave Symposium Digest 93.1 (1993 Vol. I [MWSYM]): 293-296.

Results on large signal modeling efforts of a novel MOSFET technology for L-band RF applications will be presented. A parameter extraction procedure which yields accurate RF MOS large-signal models using DC and s-parameter data is presented along with a comparison of measured and modeled class-B amplifier, mixer and s-parameter data.

❑ Return to main document.

Click on title for a complete paper.